#### **CMPD7000**

### SURFACE MOUNT DUAL, IN SERIES SILICON SWITCHING DIODES



www.centralsemi.com

# **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPD7000 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, connected in a series configuration, designed for high speed switching applications.

**MARKING CODE: C5C** 



#### **SOT-23 CASE**

MAXIMUM RATINGS: (T <sub>A</sub> =25°C)	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	V
Average Forward Current	IO	200	mA
Peak Forward Current	$I_{FM}$	500	mA
Power Dissipation	$P_{D}$	350	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	$\Theta_{JA}$	357	°C/W

# **ELECTRICAL CHARACTERISTICS PER DIODE:** (TA=25°C unless otherwise noted)

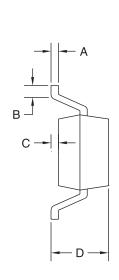
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{R}$	V <sub>R</sub> =50V			300	nA
$I_{R}$	V <sub>R</sub> =50V, T <sub>A</sub> =125°C			100	μΑ
$I_{R}$	V <sub>R</sub> =100V			500	nA
$BV_R$	I <sub>R</sub> =100μA	100			V
$V_{F}$	I <sub>F</sub> =1.0mA	0.55		0.70	V
$V_{F}$	I <sub>F</sub> =10mA	0.67		0.82	V
$V_{F}$	I <sub>F</sub> =100mA	0.75		1.10	V
$C_T$	V <sub>R</sub> =0, f=1.0MHz		1.5	2.6	pF
t <sub>rr</sub>	$I_R=I_F=10$ mA, $R_L=100\Omega$ , Rec. to 1.0mA		2.0	4.0	ns

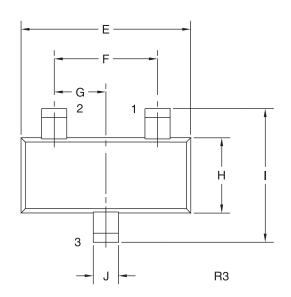
#### **CMPD7000**

### SURFACE MOUNT **DUAL, IN SERIES SILICON SWITCHING DIODES**

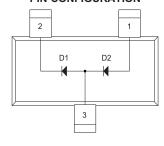


# **SOT-23 CASE - MECHANICAL OUTLINE**





#### **PIN CONFIGURATION**



# LEAD CODE:

- 1) Anode D2 2) Cathode D1
- 3) Anode D1, Cathode D2

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DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
Α	0.003	0.007	0.08	0.18			
В	0.006	-	0.15	-			
С	-	0.005	-	0.13			
D	0.035	0.043	0.89	1.09			
Е	0.110	0.120	2.80	3.05			
F	0.075		1.90				
G	0.037		0.95				
Н	0.047	0.055	1.19	1.40			
	0.083	0.098	2.10	2.49			
J	0.014	0.020	0.35	0.50			

SOT-23 (REV: R3)

R7 (27-January 2010)